Full Marks: 100

B.E. INSTRUMENTATION AND ELECTRONICS ENGINEERING FOURTH YEAR FIRST SEMESTER EXAM 2024

VLSI DESIGN

Module 1: Answer any two questions [40] 1.a) Consider the MOS structure that consists of a p-type doped Si substrate, a SiO₂ layer and a metal (Al) gate. The equilibrium Fermi potential of the doped Si substrate is $q\phi_{Fp}$ —0.2eV. Using electron affinity for Si & work function for Al given in figure, Calculate the built in potential difference 5 across MOS system. b) Deduce the expression of thickness and charge density in the depletion region of the 15 MOSFET. 2. a) Describe the various capacitances that develop in different regions of the MOSFET. 5 15 b) Derive the threshold voltage expression of the MOSFET. 3. a) Discuss channel length modulation of MOS transistor. 6 b) Discuss substrate bias effect of a MOS transistor. 4 10 c) Write a short note about BiCMOS.

Module 2:[20]

Time: Three Hours

4. Discuss twin tube fabrication process for MOSFET with neat diagram. 20

Module -3: Answer anyone questions [20]

5. a) Design a full adder circuit using CMOS.
b) Discuss cascading problem of dynamic logic gates.
c) Design domino logic for the expression Y = A + (B.C)
d) Describe the operation of a pass transistor.

6. a) Describe the CMOS stick diagram design rules and draw the stick diagram for the expression

$$Y = \overline{(A.B + C.D + E)}$$

5

5

b) Design positive edge-triggered master-slave register. 5

c) Design 16x1 MUX using pass transistor.

d) Design D flip-flop using pass transistor. 5

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- 7. a) Write a short note about lamda (λ) and micron (μ) rules. 4
 - b) Discuss Shannon's expansion theorem. 3+3

 $f(w,x,y,z)=\sum (0,1,2,3,4,11,12,15)$. Using the residue map, find the residues of f(w,x,y,z) with respect to $Y=\{w,x,y\}$.

Module -4: [20]

- 8. a) What is 'Design for Testability', and why do we need it? 5
 - b) What is the difference between Verification and Testing? 5
 - c) What is Fault Modeling? Why is Fault Model needed? 5+5